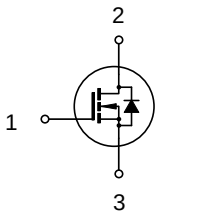
94A, 100V N-CHANNEL MOSFET

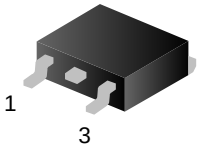
DESCRIPTION

SVGQ109R5NAD is an N-channel enhancement mode power MOS field effect transistor which is produced using Silan's LVMOS technology. The improved process and cell structure have been especially tailored to minimize on-state resistance, provide superior switching performance and high avalanche breakdown tolerance.

This device is widely used in power management for UPS and Inverter Systems.



1.Gate 2.Drain 3.Source



TO-252-2L

FEATURES

- 94A, 100V, $R_{DS(on)(typ.)}$=7.2mΩ@V_{GS}=10V
- Low gate charge
- Low Crss
- Fast switching
- Extreme dv/dt rated
- 100% avalanche tested
- Pb-free lead plating
- RoHS compliant
- Max. junction temperature: $T_{jmax.}$ =175 ºC

KEY PERFORMANCE PARAMETERS

Characteristics	Ratings	Unit
V_{DS}	100	V
$V_{GS(th)}$	1.4~2.4	V
$R_{DS(on),max}$	9.5	mΩ
I_D	94	A
$Q_{g.typ}$	49	nC

ORDERING INFORMATION

Part No.	Package	Marking	Hazardous Substance Control	Packing Type
SVGQ109R5NADTR	TO-252-2L	Q109R5NA	Halogen free	Tape & Reel

ABSOLUTE MAXIMUM RATINGS (UNLESS OTHERWISE NOTED, T_J=25°C)

Characteristics	Symbol	Test conditions	Ratings			Unit
			Min.	Typ.	Max.	
Drain-source Voltage	V_{DS}	--	100	--	--	V
Gate-source Voltage	V_{GS}	--	-20	--	20	V
Drain Current (Note 1)	I_D	T_C=25°C	--	--	94	A
		T_C=100°C	--	--	66	
Drain Current Pulsed (Note 2)	I_{DM}	T_C=25°C	--	--	376	A
Power Dissipation (Note 3)	P_D	T_C=25°C	--	--	107	W
Single Pulsed Avalanche Energy	E_{AS}	L=0.5mH, V_{DD}=80V, R_G=25Ω, starting temperature T_J=25°C	--	--	240	mJ
Single Pulsed Avalanche Current	I_{AS}	--	--	--	31	A
Operation Junction Temperature Range	T_J	--	-55	--	175	°C
Storage Temperature Range	T_{stg}	--	-55	--	175	°C

THERMAL CHARACTERISTICS

Characteristics	Symbol	Test conditions	Ratings			Unit
			Min.	Typ.	Max.	
Thermal Resistance, Junction-case, Bottom	$R_{\theta JC}$	--	--	--	1.4	°C/W
Thermal Resistance, Junction-ambient	$R_{\theta JA}$	--	--	--	62.0	°C/W
Soldering Temperature(SMD)	T_{sold}	Reflow soldering: 10±1 sec, 3times	--	--	260	°C

ELECTRICAL CHARACTERISTICS (UNLESS OTHERWISE NOTED, T_J=25°C)

Static characteristics

Characteristics	Symbol	Test conditions	Ratings			Unit
			Min.	Typ.	Max.	
Drain-source Breakdown Voltage	BV_{DSS}	V_{GS}=0V, I_D=250μA	100	--	--	V
Drain-source Leakage Current	I_{DSS}	V_{DS}=100V, V_{GS}=0V, T_J=25°C	--	--	1.0	μA
		V_{DS}=100V, V_{GS}=0V, T_J=125°C	--	3.0	--	
Gate-source Leakage Current	I_{GSS}	V_{GS}=±20V, V_{DS}=0V	--	--	±100	nA
Gate Threshold Voltage	$V_{GS(th)}$	V_{GS}=V_{DS}, I_D=250μA	1.4	--	2.4	V
Static Drain-source On State Resistance	$R_{DS(on)}$	V_{GS}=10V, I_D=39A	--	7.2	9.5	mΩ
		V_{GS}=4.5V, I_D=39A	--	9.5	13.5	
Gate Resistance	R_g	f=1MHz	--	1.9	--	Ω

Dynamic characteristics

Characteristics	Symbol	Test conditions	Ratings			Unit
			Min.	Typ.	Max.	
Input Capacitance	C_{iss}	f=1MHz, V_{GS}=0V, V_{DS}=50V	--	3321	--	pF
Output Capacitance	C_{oss}		--	390	--	
Reverse Transfer Capacitance	C_{rss}		--	7.2	--	
Turn-on Delay Time	$t_{d(on)}$	V_{DD}=50V, V_{GS}=10V, R_G=4.7Ω, I_D=39A (Notes 4, 5)	--	15	--	ns
Turn-on Rise Time	t_r		--	33	--	
Turn-off Delay Time	$t_{d(off)}$		--	51	--	
Turn-off Fall Time	t_f		--	12	--	
Total Gate Charge	Q_g	V_{DD}=50V, V_{GS}=10V, I_D=39A (Notes 4, 5)	--	49	--	nC
Gate-source Charge	Q_{gs}		--	14	--	
Gate-drain Charge	Q_{gd}		--	7.0	--	
Gate-plateau Voltage	$V_{plateau}$		--	4.0	--	V

Reverse diode characteristics

Characteristics	Symbol	Test conditions	Ratings			Unit
			Min.	Typ.	Max.	
Continuous Diode Forward Current	I_S	Integral reverse P-N junction diode in the MOSFET	--	--	94	A
Diode Pulse Current	$I_{S,pulse}$		--	--	376	
Source-Drain Diode Voltage Drop	V_{SD}	I_S=78A, V_{GS}=0V	--	--	1.4	V
Reverse Recovery Time	T_{rr}	I_S=12A, V_{GS}=0V, V_R=50V, dI_F/dt=100A/μs (Note 4)	--	64	--	ns
Reverse Recovery Charge	Q_{rr}		--	115	--	nC

Notes:

1. The rated value only refers to the maximum absolute value at the case temperature of 25°C in the specification. If the case temperature is higher than 25°C, it should be derated according to the actual environmental conditions
2. Pulse time 5μs;
3. The dissipation power will change with temperature, derating above 25°C: 0.71W/°C;
4. Pulse Test: Pulse width ≤300μs, Duty cycle≤2%;
5. Essentially independent of operating temperature.

TYPICAL CHARACTERISTICS

Figure 1. Output Characteristics

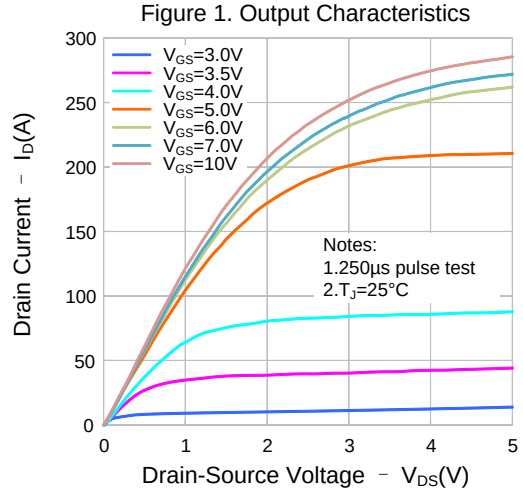


Figure 2. Transfer Characteristics

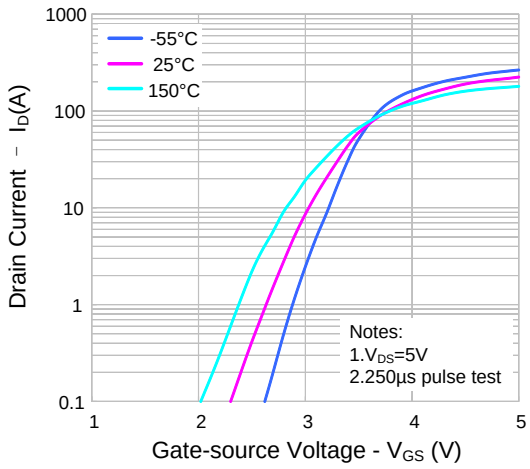


Figure 3. On-resistance vs. Drain Current

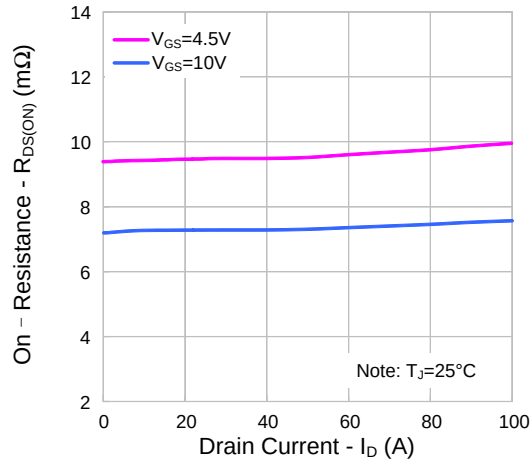


Figure 4. On-resistance vs. Gate-source Voltage

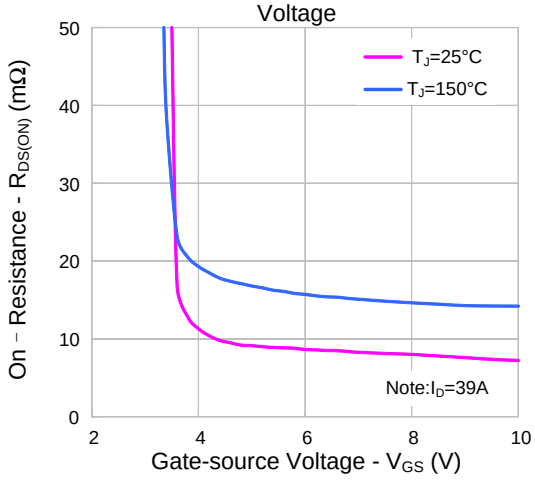


Figure 5. Gate-source Turn-on Voltage vs. Temperature characteristics

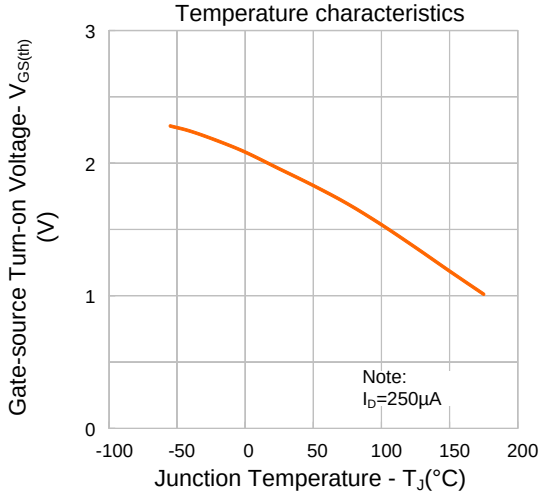
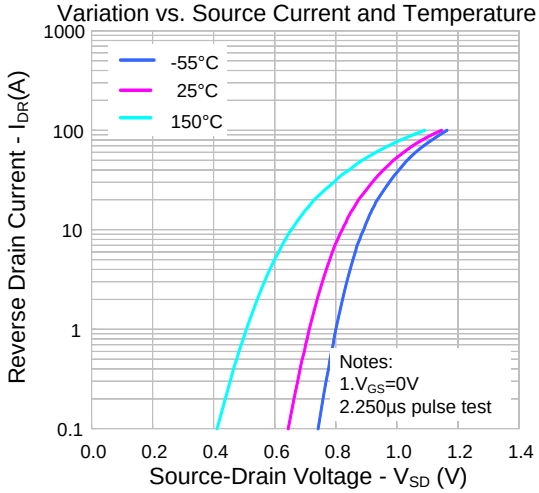


Figure 6. Body Diode Forward Voltage Variation vs. Source Current and Temperature



TYPICAL CHARACTERISTICS (CONTINUED)

Figure 7. Capacitance Characteristics

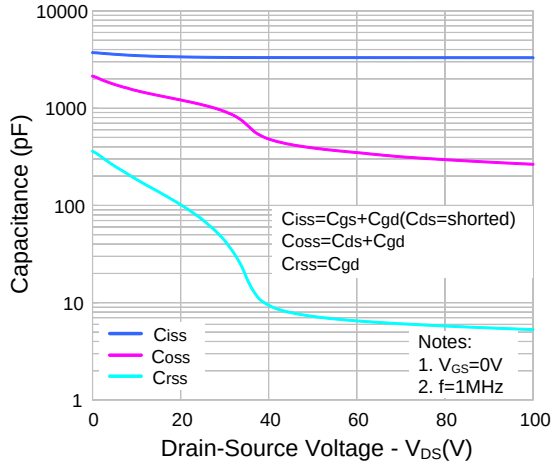


Figure 8. Gate Charge

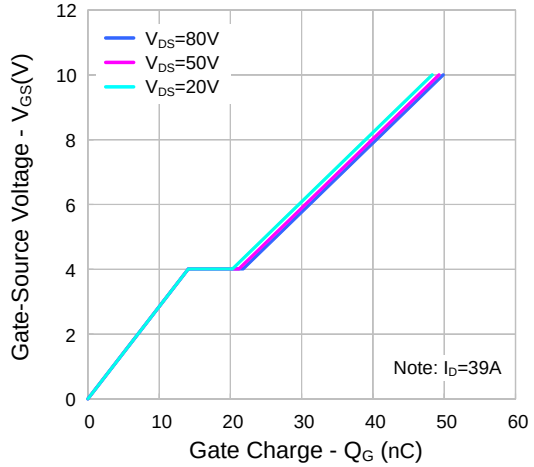


Figure 9. Breakdown Voltage Variation vs. Temperature

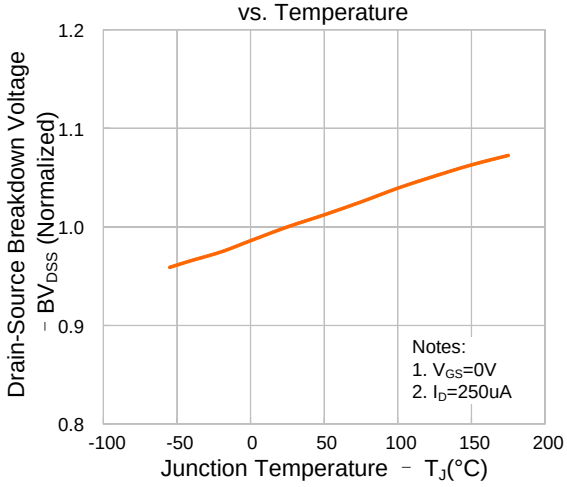


Figure 10. On-resistance Variation vs. Temperature

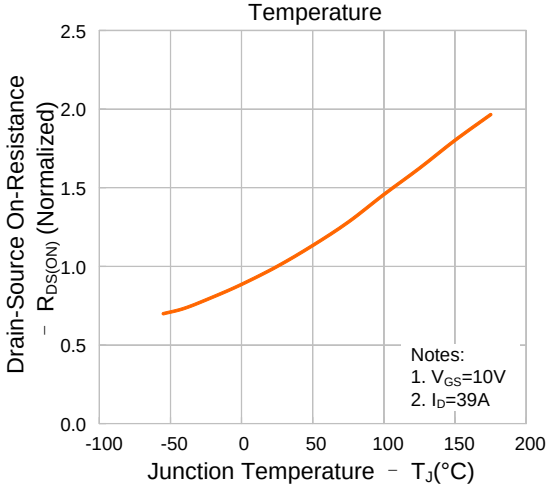


Figure 11. Max. Safe Operating Area

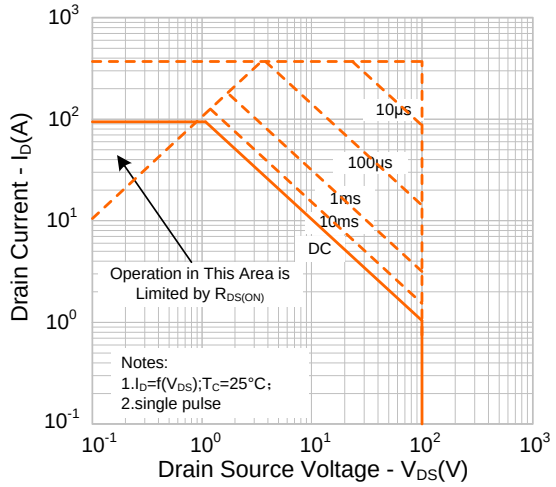
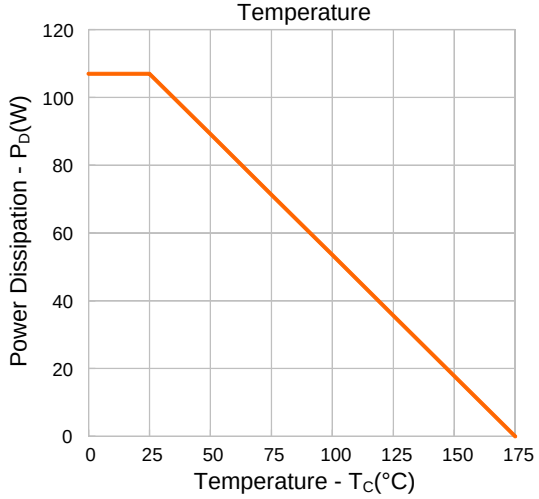


Figure 12. Power Dissipation vs. Case Temperature



TYPICAL CHARACTERISTICS (CONTINUED)

Figure 13. Drain Current vs. Case Temperature

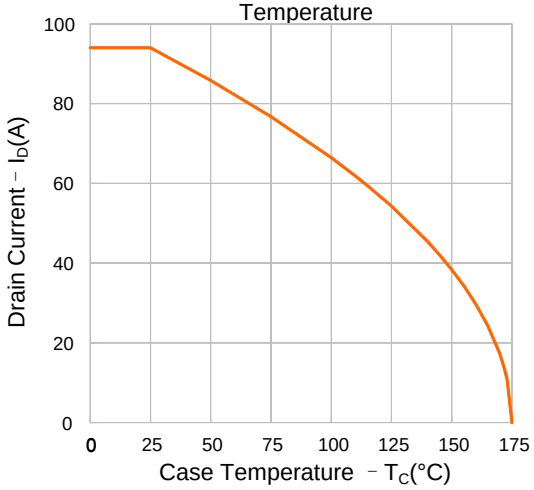
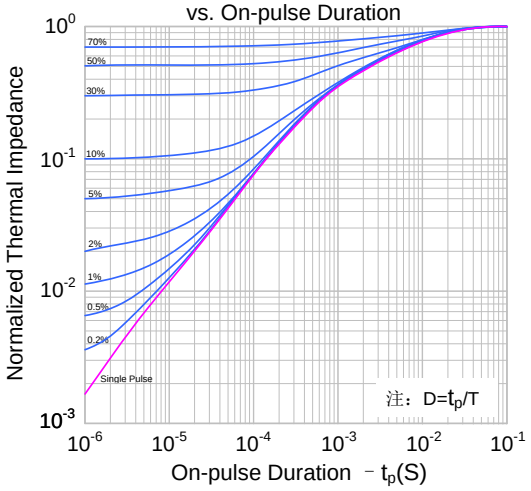
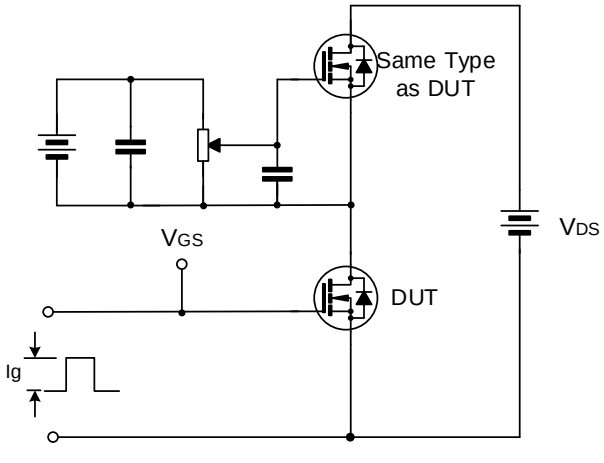


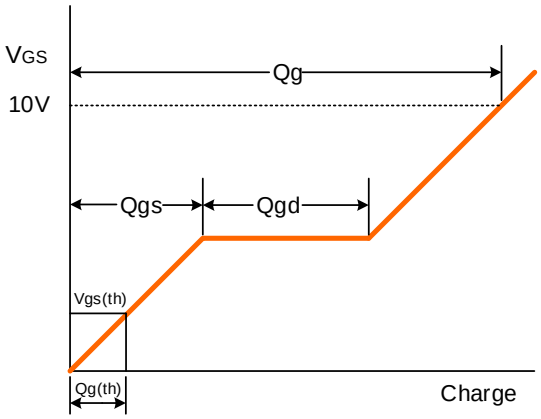
Figure 14. Transient Thermal Impedance vs. On-pulse Duration



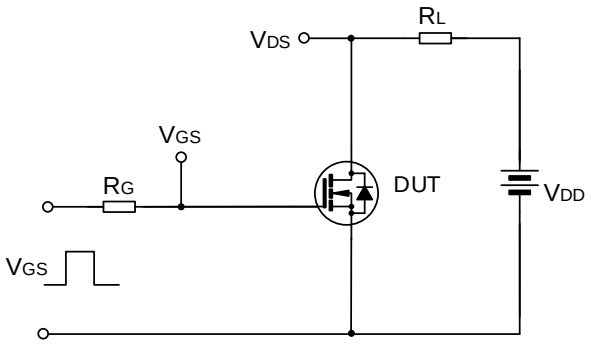
TYPICAL TEST CIRCUIT

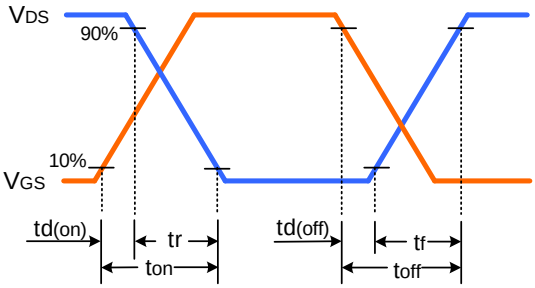
Gate Charge Test Circuit & Waveform



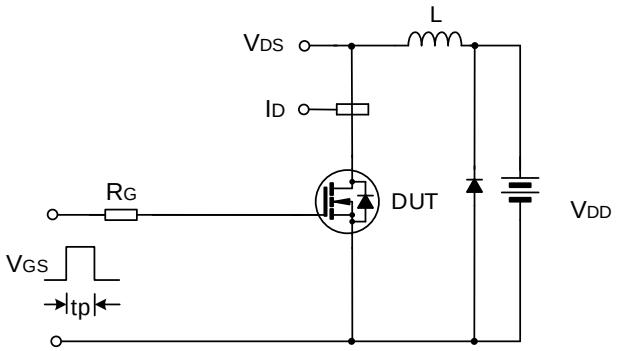


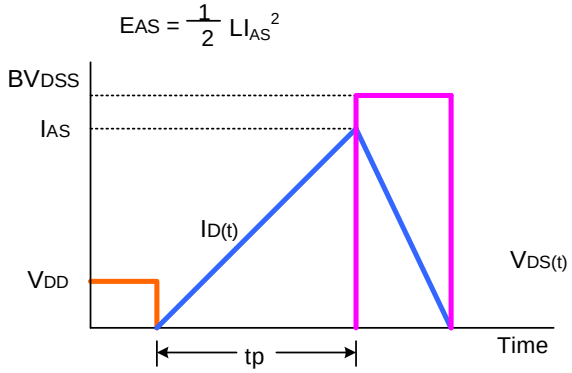
Resistive Switching Test Circuit & Waveform





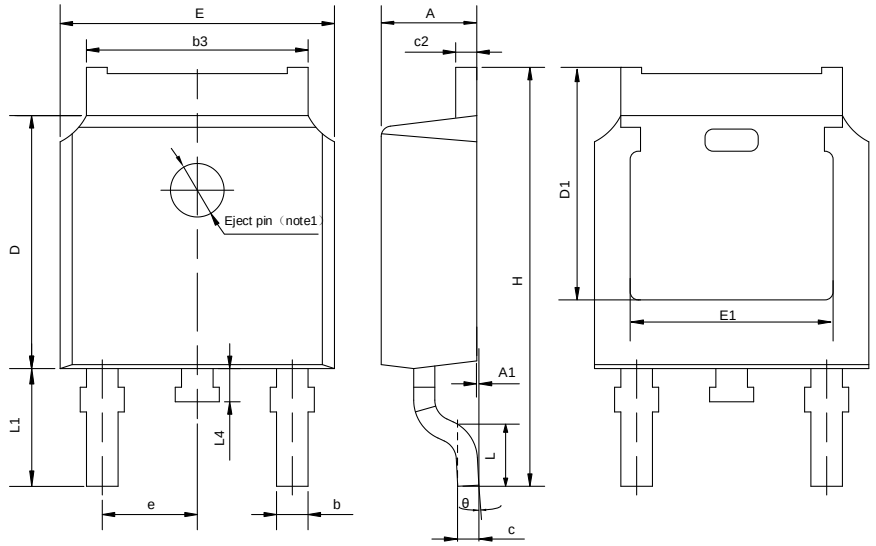
Unclamped Inductive Switching Test Circuit & Waveform





PACKAGE OUTLINE

TO-252-2L **UNIT: mm**



SYMBOL	MILLIMETER		
	MIN	NOM	MAX
A	2.20	2.30	2.38
A1	0	—	0.10
b	0.72	0.76	0.85
b3	5.13	5.33	5.46
c	0.47	0.51	0.60
c2	0.47	0.51	0.60
D	6.00	6.10	6.20
D1	5.00	5.24	5.60
E	6.50	6.60	6.70
E1	5.15	5.35	5.55
e	2.186	2.286	2.386
H	9.80	10.10	10.40
L	1.40	1.50	1.70
L1	2.70	2.90	3.10
L4	0.60	0.80	1.00
θ	0°	—	8°

MOS DEVICES OPERATE NOTES:

Electrostatic charges may exist in many things. Please take following preventive measures to prevent effectively the MOS electric circuit as a result of the damage which is caused by discharge:

- The operator must put on wrist strap which should be earthed to against electrostatic.
- Equipment cases should be earthed.
- All tools used during assembly, including soldering tools and solder baths, must be earthed.
- MOS devices should be packed in antistatic/conductive containers for transportation.

Important notice :

1. Silan reserves the right to make changes of this instruction without notice.
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Rev.: 1.1

Revision History:

1. Delete the wave soldering condition
2. Add Figure 13
3. Update the typical test circuit
4. Update the package outline
5. Update the important notice

Rev.: 1.0

Revision History:

1. First release